





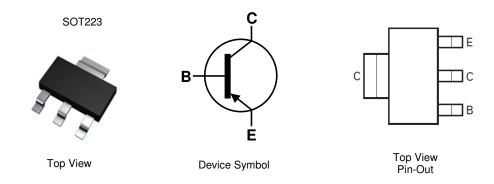
400V PNP HIGH VOLTAGE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -400V
- I_C = -500mA High Continuous Current
- I_{CM} = 1A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < 250mV @ 50mA
- hFE > 40 Specified up to 200mA for High Current Gain Hold Up
- Complementary NPN Type: FZT658
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads;
- Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

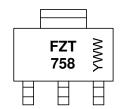
Ī	Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
	FZT758TA	FZT758	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information

SOT223



FZT 758 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-400	٧
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-0.5	Α
Peak Pulse Current	I _{CM}	-1	Α

Thermal Characteristics (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)		2.0	W	
Power Dissipation	(Note 7)	P_D	1.6		
	(Note 8)] [1.2		
	(Note 5)	- R _{eJA}	41.7		
Thermal Resistance, Junction to Ambient	(Note 6)		62.5	°C/W	
Thermal nesistance, junction to Ambient	(Note 7)		78.1		
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ heta JL}$	12.9		
Operating and Storage Temperature Range	T_{J} , T_{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

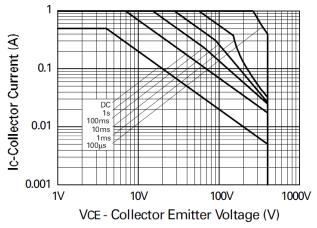
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

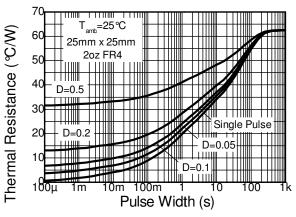




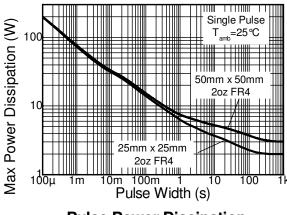
Thermal Characteristics and Derating Information



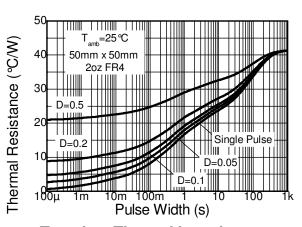
Safe Operating Area



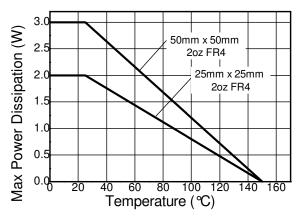
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Derating Curve





Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

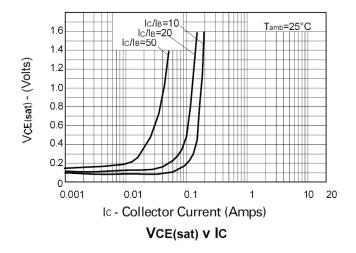
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-400	_	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-400	-	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	-	-	-100	nA	V _{CB} = -320V
Collector Cut-Off Current	I _{CES}	_	-	-100	nA	V _{CE} = -320V
Emitter Cut-Off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -4V
	V _{CE(sat)}	-	-	-0.30	V	$I_C = -20mA$, $I_B = -1mA$
Collector-Emitter Saturation Voltage (Note 11)				-0.25		$I_C = -50 \text{mA}, I_B = -5 \text{mA}$
				-0.50		I _C = -100mA, I _B = -10mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	-	-0.9	V	I _C = -100mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	_	-1.0	V	I _C = -100mA, V _{CE} = -5V
	h _{FE}	50	_	-		$I_C = -1 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Gain (Note 11)		50	-	_	_	$I_{C} = -100 \text{mA}, V_{CE} = -5 \text{V}$
		40	_	_		I _C = -200mA, V _{CE} = -10V
Current Gain-Bandwidth Product (Note 11)	f _T	50	-	-	MHz	V _{CE} = -20V, I _C = -20mA, f = 20MHz
Output Capacitance (Note 11)	C _{obo}	-	-	20	pF	V _{CB} = -20V, f = 1MHz
Switching Times	ton	-	140	-	no	I _C = -100mA, V _{CC} = -100V
Switching Times	t _{off}	_	2,000	_	ns	$I_{B1} = 10mA$, $I_{B2} = -20mA$

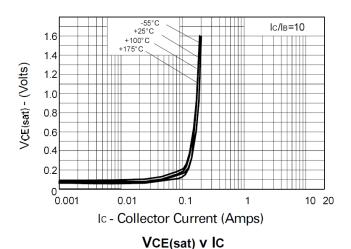
Note:

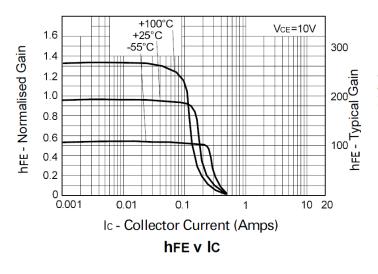
11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

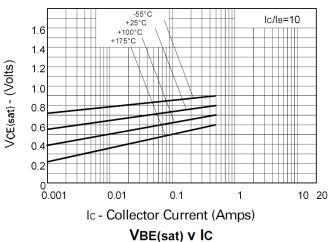


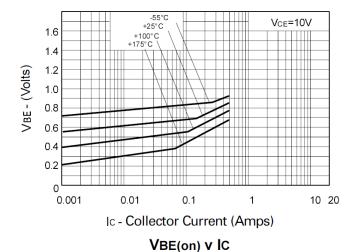
Typical Electrical Characteristics (@T_A = +25 ℃, unless otherwise specified.)









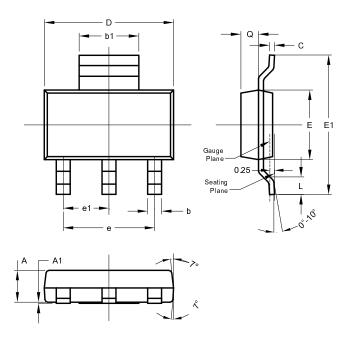






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

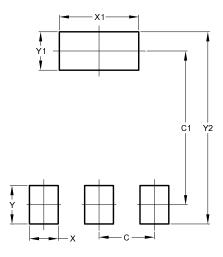


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_		2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT223



Dimensions	Value (in mm)		
C	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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